LAPT 2SC3264

Silicon NPN Epitaxial Planar Transistor (Complement to type 2SA1295)

Application: Audio and General Purpose

Absolute maximum ratings (Ta=25°C)

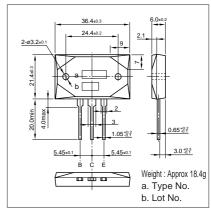
Symbol	2SC3264	Unit		
Vсво	230	V		
VCEO	230	V		
VEBO	5	V		
Ic	17	Α		
Ів	5	Α		
Pc	200(Tc=25°C)	W		
Tj	150	°C		
Tstg	-55 to +150	°C		

Electrical Characteristics

	iai aotoriotioo	(Ta=25 0)			
Symbol	Conditions	2SC3264	Unit		
Ісво	Vcb=230V	100max	μА		
І ЕВО	VEB=5V	100max	μΑ		
V(BR)CEO	Ic=25mA	c=25mA 230min			
hfe	Vce=4V, Ic=5A	50min*			
Vce(sat)	Ic=5A, IB=0.5A	2.0max	V		
fT	VcE=12V, IE=-2A 60typ		MHz		
Сов	Vcb=10V, f=1MHz	250typ	pF		

*hfe Rank \overline{O} (50 to 100), Y(70 to 140)

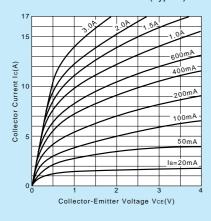
External Dimensions MT-200



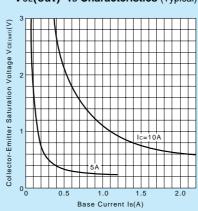
■Typical Switching Characteristics (Common Emitter)

,	Vcc (V)	Rι (Ω)	Ic (A)	V _{BB1} (V)	VBB2 (V)	I _{B1} (A)	IB2 (A)	ton (µs)	tstg (µs)	tf (µs)
	60	12	5	10	-5	0.5	-0.5	0.30typ	2.40typ	0.50typ

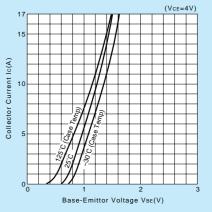
Ic-VcE Characteristics (Typical)



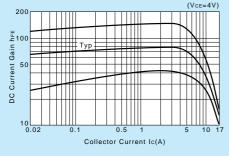
VcE(sat)-IB Characteristics (Typical)



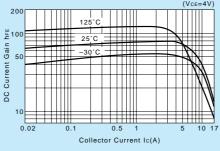
Ic-VBE Temperature Characteristics (Typical)



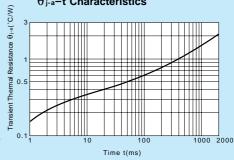
hfe-Ic Characteristics (Typical)



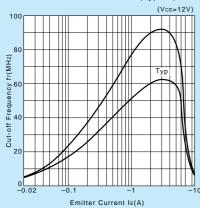
hfe-Ic Temperature Characteristics (Typical)



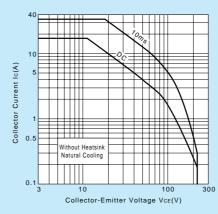
θ_{j-a}-t Characteristics



fT-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc-Ta Derating

